Thermoelectric Power Factor of Ultra-Narrow Silicon Nanowires

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INTRODUCTION

The thermoelectric performance of materials is determined by the figure of merit $ZT=\sigma S^2/(\kappa_e+\kappa_l)$, where σ is the electrical conductivity, S is the Seebeck coefficient and κ_e and κ_l are the electronic and lattice contributions to the thermal conductivity, respectively. The interrelation between these quantities has traditionally kept ZT low, around unity. Nanomaterials have recently attracted significant attention because at the nanoscale the length scale degree of freedom offers possibilities of independent design of σ, S and κ_l such that high ZT values can be achieved. This was demonstrated to be the case not only for the rare-earth and/or toxic usual TE materials, but also for traditionally poor TE materials such as Si. Bulk Si has a very high κ_l=140W/mK which results to ZT~0.01 at 300K. Silicon nanowires (NWs), on the other hand, have demonstrated ZT~1 (Fig. 1) [1, 2], which makes Si a promising and abundant TE material candidate with well established industrial scaling processes.

METHOD AND DISCUSSION

Although most of the benefits in the ZT of Si NWs have resulted from the drastic reduction in κ_l down to 2W/mK, it is becoming evident that benefits from κ_l are reaching their limits, and further TE performance improvement will result from power factor (σS^2) improvements. In this work we present a comprehensive analysis of the thermoelectric power factor in Si NWs of different carrier type (n- and p-type), different diameters, and different transport and confinement orientations (Fig. 2). We employ atomistic tight-binding techniques (the $sp^3d^5s^*$ model) and linearized Boltzmann transport [3]. We identify the design parameters that have the strongest influence on the power factor and identify bandstructure optimization directions. Our conclusions should be relevant for the optimal design of the TE power factor of low dimensional materials in general.

The Seebeck coefficient in NWs depends at first order on the distance of the band edges form the Fermi level, η_F. At a constant carrier concentration this changes differently for different NW types as a function of the NW diameter, mainly increasing (Fig. 3a). This increase improves the power factor as the diameter is reduced below D=7nm as shown in Fig. 3b (under ballistic conditions). Additionally, the carrier velocities are a strong function of NW type and can vary differently as the diameter is reduced. In some cases the carrier velocities are diameter independent (Fig. 3c), but in other cases they increase with diameter reduction (Fig. 3d).

Such property differences could be used to optimize the thermoelectric performance of NWs. For example, although under ballistic conditions the Seebeck coefficient can offer some advantages to the power factor, when phonons and surface roughness scattering (SRS) is considered, the conductivity is severely degraded with diameter reduction (Fig. 4a), and the ZT is degraded (Fig. 4c). On the other hand, however, in cases where the carrier velocity increases with confinement, such as in p-type [111] NWs, the conductivity increases (Fig. 5a), it compensates for SRS and improved ZT values can be obtained (Fig. 5c).

CONCLUSION

Ultra-thin Si NWs offer the possibility of TE power factor optimization through bandstructure engineering techniques. The Seebeck coefficient and the electrical conductivity can be optimized using confinement and orientation to achieve enhanced TE properties.

ACKNOWLEDGEMENT

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REFERENCES

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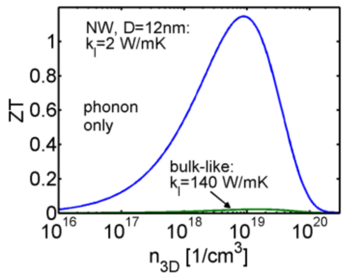

Fig. 1. The ZT figure of merit versus carrier concentration of a cylindrical NW of D=12nm calculated for k_l=2 W/mK (NW-like), and k_l=140 W/mK (bulk-like).

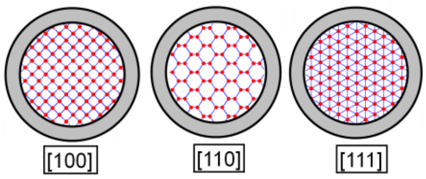

Fig. 2. Cross sections of the NWs analysed. The [100], [110] and [111] orientations. The NW surface is assumed to be hydrogen passivated.

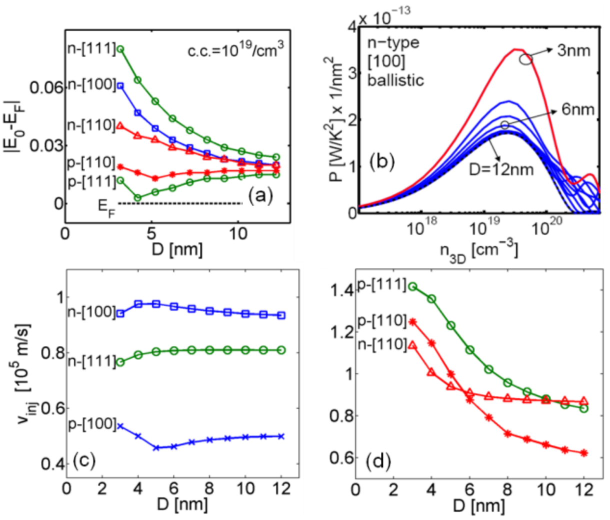

Fig. 3. (a) The shift in the band edge of n- and p-type NWs in different transport orientations versus diameter, at carrier concentration 10^{19}/cm^3. (b) The power factor of n-type [100] NWs versus carrier concentration for diameters D=12nm down to D=3nm. (c-d) The carrier injection velocities versus diameter of n- and p-type NWs of different transport orientations.

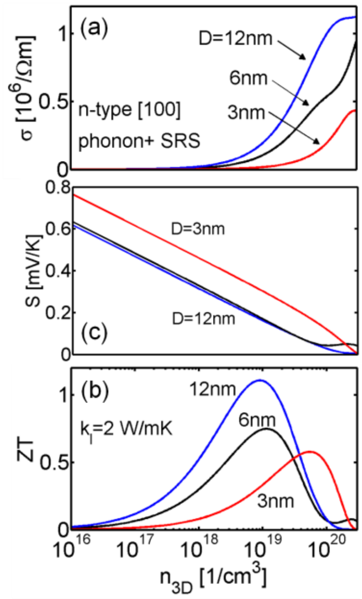

Fig. 4. Thermoelectric coefficients versus carrier concentration for n-type [100] NWs of D=12nm (blue), 6nm (black) and 3nm (red), at 300K. Phonon scattering plus SRS are included. (a) The electrical conductivity. (b) The Seebeck coefficient. (c) The ZT figure of merit (k_l=2 W/mK is assumed for all cases).

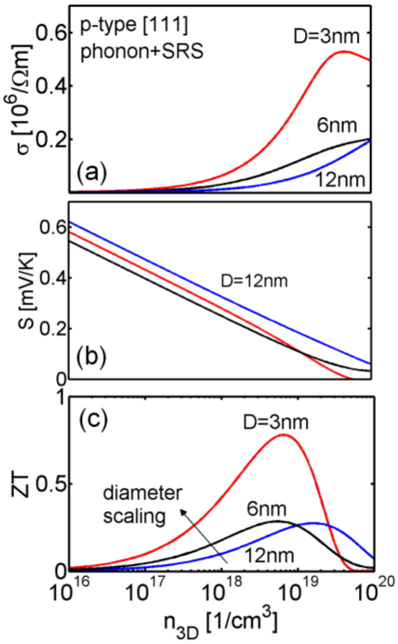

Fig. 5. Thermoelectric coefficients versus carrier concentration for p-type [111] NWs of D=12nm (blue), 6nm (black) and 3nm (red), at 300K. Phonon scattering plus SRS are included. (a) The electrical conductivity. (b) The Seebeck coefficient. (c) The ZT figure of merit (k_l=2 W/mK is assumed for all cases).